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60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	19.5mΩ @ V _{GS} = 10V	7.6A
	28mΩ @ V _{GS} = 4.5V	6.2A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch
- Adaptor Switch
- Notebook PC

Features and Benefits

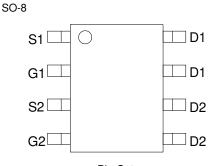
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH6016LSDQ)

Mechanical Data

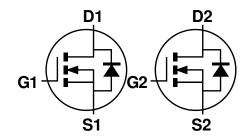
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.076 grams (Approximate)







Pin-Out Top View



Equivalent Circuit

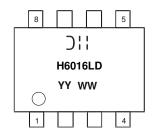
Ordering Information (Note 4)

- 7			
	Part Number	Case	Packaging
	DMTH6016LSD-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
H6016LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	7.6 5.4	Α
Continuous Drain Current (Note 6) V _{GS} = 4.5V	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	6.2 4.4	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	40	Α	
Maximum Continuous Body Diode Forward Current	Is	1.7	Α	
Pulsed Body Diode Forward Current (10µs pulse, duty cycle = 1%)		I _{SM}	40	Α
Avalanche Current, L = 0.1mH		I _{AS}	15.3	Α
Avalanche Energy, L = 0.1mH		E _{AS}	11.7	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	103	°C/W
Total Power Dissipation (Note 6)	P _D	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	77	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	14.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1		2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	15	19.5	mΩ	$V_{GS} = 10V, I_{D} = 10A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	21	28		$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	864	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	282	_	pF		
Reverse Transfer Capacitance	Crss	_	27	_			
Gate Resistance	R_g	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.4	_		V _{DS} = 30V, I _D = 10A	
Total Gate Charge (V _{GS} = 10V)	Q_g	_	17	_	nC		
Gate-Source Charge	Q _{gs}	_	3.1	_	IIC		
Gate-Drain Charge	Q_{gd}	_	4.3	_			
Turn-On Delay Time	t _{D(ON)}	_	3.4	_		$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 10A$	
Turn-On Rise Time	t _R	_	5.2	_			
Turn-Off Delay Time	t _{D(OFF)}	_	13	_	ns		
Turn-Off Fall Time	t _F	_	7	_			
Reverse Recovery Time	t _{RR}	_	22	_	ns	1 40A -12/-14 400A/	
Reverse Recovery Charge	Q _{RR}	_	11	_	nC	$I_F = 10A$, di/dt = 100A/ μ s	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

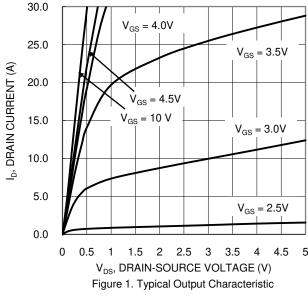
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.







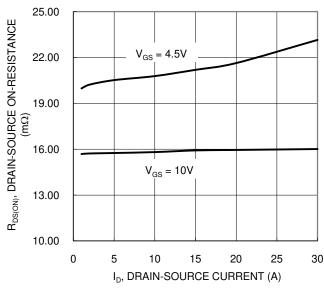


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

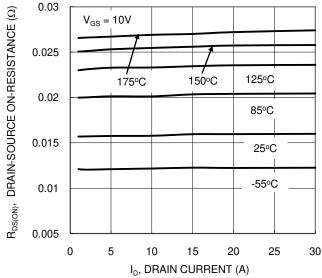
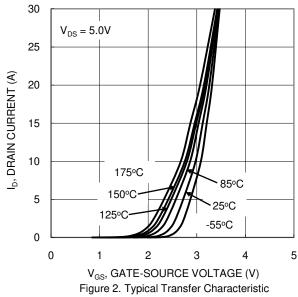


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



50 45

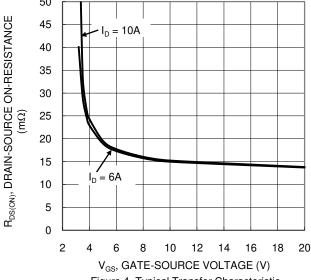


Figure 4. Typical Transfer Characteristic

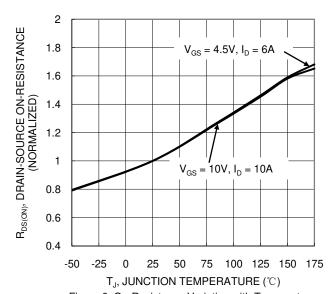


Figure 6. On-Resistance Variation with Temperature





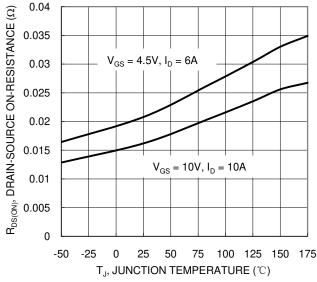


Figure 7. On-Resistance Variation with Temperature

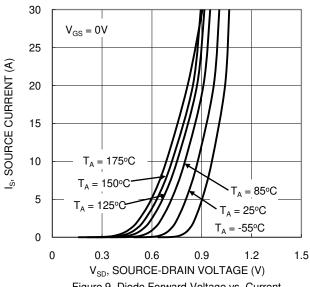


Figure 9. Diode Forward Voltage vs. Current

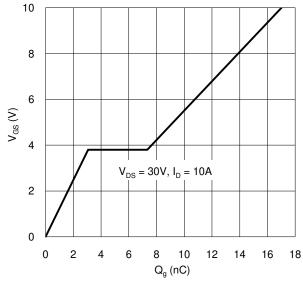


Figure 11. Gate Charge

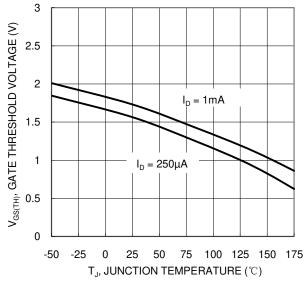
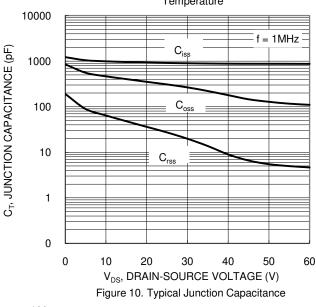
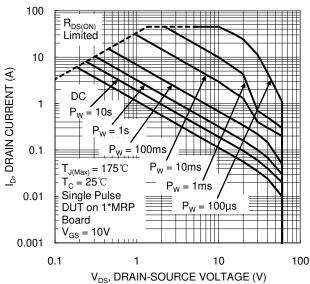


Figure 8. Gate Threshold Variation vs. Junction Temperature







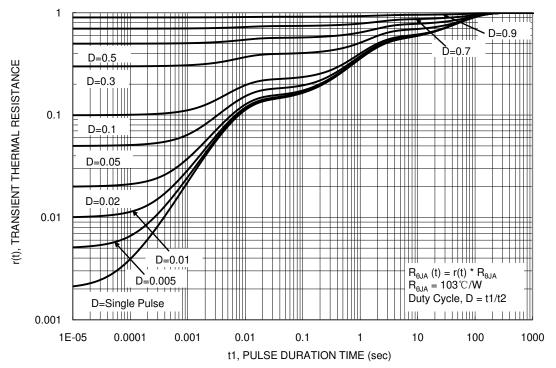


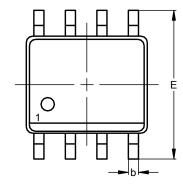
Figure 13. Transient Thermal Resistance

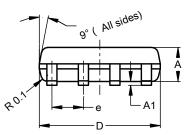


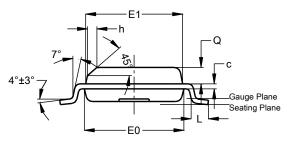
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





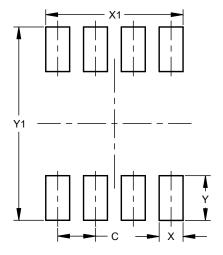


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A 1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)		
С	1.27		
Х	0.802		
X1	4.612		
Υ	1.505		
Y1	6.50		



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